Emerging edge states on the surface of the epitaxial semimetal CuMnAs thin film

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Abstract

Epitaxial thin films of CuMnAs have recently attracted attention due to their potential to host relativistic antiferromagnetic spintronics and exotic topological physics. Here we report on the structural and electronic properties of a tetragonal CuMnAs thin film studied using scanning tunneling microscopy (STM) and density functional theory (DFT). STM reveals a blend of surface domains corresponding to two kinds of As-terminated surface reconstructions, and both domains show the expected semi-metallic behavior. An unexpected zigzag step edge surface reconstruction is observed with emerging electronic states below the Fermi energy. DFT calculations indicate that the step edge reconstruction can be attributed to an As deficiency that results in changes in the density of states of the remaining As atoms at the step edge. Our work provides a detailed understanding of the surface structure and step edges on the CuMnAs thin film, enabling in-depth studies of its topological properties and magnetism.
Introduction

Antiferromagnetic (AFM) tetragonal CuMnAs thin films possess many potential advantages in spintronics applications [1-3]. The AFM spin states in CuMnAs can be efficiently and reversibly controlled with an applied electrical current using current-induced spin orbit torques [2]. In addition, antiferromagnetic devices using these materials would have upper speed limits which are two to three orders of magnitude greater than ferromagnets for domain switching [3], and domain wall motion [4, 5]. Furthermore, they exhibit inherently multi-stable domain configurations useful for neuromorphic computing [6, 7]. On the fundamental side, CuMnAs is predicted to be an exotic magnetic Dirac semimetal; where the Dirac crossing in the band structure can be manipulated using electrically controlled magnetic order [8-10]. As a result, CuMnAs is a particularly interesting candidate material for studying the relationship between Dirac fermions and magnetism as well as for exploring topological metal-insulator transitions (MIT) driven by a Néel vector [8]. However, little is known about the surface morphology, intrinsic defects, and electronic properties of the CuMnAs, all which plays an important role for its magnetic properties and device performance, and is a prerequisite for the further understanding of its topological physics. In this regard, scanning tunneling microscopy (STM), an essential technique for probing the local electronic and magnetic structure of materials especially at the surface, is highly desirable for revealing direct correlations between surface morphology, microscopic defects, and electronic and magnetic behaviors [11-14].

Here we report STM studies of a tetragonal CuMnAs thin film grown epitaxially on a GaP(001) substrate [2]. The atomically resolved STM images reveal a blend of different surface domains corresponding to two kinds of As-terminated surface reconstructions. The local density of states (LDOS) confirms the semi-metallic behavior of CuMnAs. Interestingly, the clean step edge displays a zigzag periodic structure with a doubling of the in-plane lattice constant, which induces localized states below
the Fermi level. DFT calculations reproduce the zigzag step structure demonstrating that, in contrast to the bulk, periodic As vacancies are more energetically favorable than Mn vacancies at the step edges. It is the presence of these As vacancies which are thought to induce changes in the electronic structure thereby driving the emerging edge states observed at the surface step in the CuMnAs film. This work brings to light the atomic and local electronic structure of CuMnAs surfaces and step edges. The understandings of these are a prerequisite for future studies on this material regarding the topological properties using angle-resolved photoemission spectroscopy (ARPES) [15, 16] and the local magnetic structure using spin-polarized STM [17]. In addition, knowledge of the surface morphology and atomic defects in the CuMnAs films may lead to improvements in device performance for antiferromagnetic memory applications [2].

Methods

A tetragonal CuMnAs thin film (20 nm thick) was grown epitaxially on a GaP (001) substrate using the molecular beam epitaxy (MBE) method [18]. The as-grown CuMnAs film was capped in situ with an amorphous As layer (thickness of 30 nm) and transferred from the MBE growth chamber to a remote ultra-high vacuum (UHV) STM system through the air. The sample was subsequently annealed at ~200 °C overnight in UHV to remove the capping layer to expose the clean surface for STM measurements. All STM measurements were performed at room temperature. Etched tungsten tips were used for both STM imaging and spectroscopy. The tips were calibrated on a clean Cu(111) crystal by resolving the Cu(111) surface states via STM spectroscopy.

All density functional theory (DFT) calculations were performed within the generalized gradient approximation (GGA) using the PBEsol exchange-correlation functional [19] and projector augmented wave potentials [20, 21] as implemented in the Vienna Ab initio Simulation Package (VASP) [22, 23].
We used a 600 eV kinetic energy cutoff and an \( 8 \times 8 \times 5 \) and \( 1 \times 4 \times 1 \) k-point grids for calculations of the bulk and step edge unit cells, respectively. To calculate the relaxed atomic geometries for the bulk CuMnAs structure, the internal forces and stress tensor components were relaxed to less than 0.001 meV/Å and 0.1 kbar, respectively. In the case of step edge model, the ionic positions were relaxed to forces <0.001 meV/Å while the in-plane lattice constants of the supercell were fixed to the computed bulk lattice constants values. To account for strong correlations between the Mn-\( d \) orbitals we employ the DFT+U approach using the double-counting correction scheme from Ref.[24] and the value \( U=2 \) eV following Ref.[25]. Both bulk and step edge models were initialized to antiferromagnetic ordering with ferromagnetic planes parallel to the (001) plane.

The vacancy formation energies \( \Delta E_{\text{vac}} \) for all systems were computed relative to the pristine system as follows:

\[
\Delta E_{\text{vac}} = E_{\text{defect}} + E_{\text{ref}} - E_{\text{pristine}},
\]

where \( E_{\text{defect}} \) is either bulk CuMnAs or the step-edge surface, in each case with an As or Mn vacancy, \( E_{\text{ref}} \) is the total energy/atom of the bulk (As or Mn) elemental reference solid, and \( E_{\text{pristine}} \) is bulk CuMnAs or the step edge surface with no vacancies. Elemental Mn in the \( L1_0 \)-phase with antiferromagnetic ordering and elemental As in the rhombohedral phase were used as the reference solids, respectively. This choice is consistent with Ref [25]
Results

**Figure 1**: (a), (b) Top and side views of the crystal structure of tetragonal CuMnAs. (c) STM topographic image of the CuMnAs surface after removing the amorphous As capping layer. The line profile crossing the steps is shown in the inset (sample bias $V_s = -2.5$ V, tunneling current $I = 50$ pA).

The crystal structure of tetragonal CuMnAs is illustrated in Fig. 1(a), (b). The lattice parameters are $c = 0.632$ nm and $a = b = 0.382$ nm. While CuMnAs in the bulk crystalline form is orthorhombic, a tetragonal phase is stabilized in a film grown by MBE [18]. A typical large-scale STM image of CuMnAs after removing the As capping layer is shown in Fig. 1(c). The annealing procedure effectively removes the amorphous As capping layer to reveal the surface steps on CuMnAs. Notably, there are still some residual contaminations on the surface as indicated by the bright spots in Fig. 1(c). Nevertheless, step edges are observed along the $a$ or $b$ directions, consistent with the square crystal symmetry of the sample and matching along the half diagonal of the unit cell of GaP substrate [18]. The small deviation is due to the thermal drift of the large-scale STM image acquired at room temperature. The inset in Fig. 1(c) shows a line profile across several steps. It took along the fast scan direction to avoid the effect from the thermal...
drift. As expected, step heights appear with an integer number of unit cell size along c direction, e.g., 0.64 nm (one unit cell) or 1.28 nm (double of a unit cell). Surprisingly, step heights of 0.30 ± 0.01 nm and 0.33 ± 0.01 nm are also observed, which are less than a unit cell size. These values of 0.30 nm and 0.33 nm correspond to the spacing between adjacent As layers as shown in Fig. 1b. Note, the spacings between Mn-Mn layers are 0.215 nm and 0.417 nm, while the spacing of Cu-Cu layers is 0.62 nm. In addition, STM spectroscopy on these different terraces are the same (to be discussed in below), which suggests that they have the same chemical termination. As a result, we determine the top surface of the CuMnAs thin film to be terminated by As atoms.

**Figure 2:** (a) Atomically resolved STM image of CuMnAs ($V_s = -2$ V, $I = 50$ pA) which demonstrates both 1×1 and 1×2 domain structures. The inset depicts a zoomed-in image of the 1×1 domain ($V_s = -1$ V, $I = 50$ pA) (Fourier filtering was applied to enhance the contrast). (b) Dual bias (~2 V & −1 V) STM image of the 1×2 surface domain reconstruction. (c) Typical dI/dV spectrum of the CuMnAs surface ($V_s = -1$ V, $I = 50$ pA, $V_{ac} = 30$ mV, $f = 1000$ Hz) which was averaged from 100 dI/dV spectra acquired consecutively to reduce the noise. There is no noticeable difference of spectra between the two different phase domains.
Figure 2(a) shows an atomically resolved STM image of the CuMnAs surface, revealing the coexistence of two kinds of domain structures labeled 1×1 and 1×2 phases on the surface. The 1×1 phase structure (Fig. 2(a) inset) shows a square lattice with a unit cell of 0.385 ± 0.005 nm, which is half of the diagonal of the GaP unit cell (GaP lattice constant of 0.545 nm), corresponding to the lattice parameter of CuMnAs epitaxially grown on a GaP(001) substrate [18]. The 1×2 phase domain corresponds to a surface reconstruction as confirmed by the dual bias (−2 V & −1 V) scanning image in Fig. 2 (b). The differential tunneling conductance dI/dV spectroscopy performed on these two domains, however, do not show any unambiguous differences. A typical dI/dV spectrum on the surface is shown in Fig. 2(c). A finite but strong suppression of the DOS is observed at the Fermi level, consistent with the predicted semi-metallic behavior in the CuMnAs samples [8].

Figure 3: (a) STM image across a step edge of CuMnAs ($V_s = -1.0$ V, $I = 50$ pA). (b) Atomically resolved zoomed-in STM image at the step edge in (a) ($V_s = -1.0$ V, $I = 50$ pA). (c), A model structure of the step edge. (d) dI/dV spectra taken along the black dashed line in (b) showing emerging states below the Fermi level near the step edge ($V_s = -1$ V, $I = 50$ pA, $V_{ac} = 30$ mV, $f = 1000$ Hz). Each curve was averaged from 100 dI/dV spectra acquired consecutively to reduce the noise.
Now we examine the electronic structures at the step edges of the surface where the crystal symmetry is further reduced. Figure 3(a) shows an STM image with a step edge (height of 0.3 nm) on the surface. Along the step edge, an interesting 1D zigzag feature is observed with a periodicity of $0.77 \pm 0.01$ nm which doubles the crystal lattice constant. The atomic resolution of As atoms is visible both on the CuMnAs surface and at the zigzag step edge as displayed in the zoomed-in image of Fig. 3b. Based on the observed images, a model structure of this step edge is proposed in Fig. 3(c). The $dI/dV$ spectra are measured along the line marked in Fig. 3(b) and shown in Fig. 3d near a step edge (black dashed arrow). Upon approaching the step edge, there is a clear enhancement of the DOS below the Fermi level down to $-0.8$ eV indicating emergence of new states at step edges.

**Figure 4:** Atomic model used for density functional theory calculations of the step edge. (a) Side view without vacancies showing the upper and lower MnAs layers. (b) Top view of the upper MnAs layer with an As vacancy. (c) Top view of the lower MnAs layer with a Mn vacancy. Blue, magenta, green, red Cu,
Mn, and As atoms, respectively. Bold outlined red or white circles represent Mn and As vacancies, respectively.

To better understand the atomic structure near the step edge and emerging edge states we compare the experimental results with DFT calculations. In particular, we simulated an atomic model of the step edge as illustrated in Fig. 4. To facilitate the comparison with experiment, we focus on a surface comprised of a lower and an upper terrace where along the a lattice vector, the lower and upper terraces are 7 and 4 unit cells wide, respectively. Both the lower and upper terraces are As-terminated with a step height of 2.835 Å consistent with the experimental observations. To describe the zigzag feature the unit cell is doubled along the b axis. A ~21 Å vacuum layer is used in the model.

<table>
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<th>Defect</th>
<th>Bulk As vacancy</th>
<th>Bulk Mn vacancy</th>
<th>Step Edge As vacancy</th>
<th>Step Edge Mn vacancy</th>
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<tr>
<td>Formation energy</td>
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<td>(+0.240)</td>
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**Table 1:** Calculated formation energies for isolated defects in bulk CuMnAs and periodic defects along the step edge as depicted in Fig.4. Formation energies for unrelaxed atomic positions are given in parenthesis.

First, we examine the thermodynamic stability of their bulk counterparts by computing the corresponding formation energies employing a 4×4×2 CuMnAs supercell with a single Mn or As vacancy. The formation energies of As and Mn vacancies in bulk are presented in Table 1. Similar to Ref.[25], we find that the formation energies of As and Mn vacancies in bulk are positive and negative, respectively. This implies that in the bulk the formation of a Mn vacancy is energetically favorable, whereas As vacancies are not likely to form.
Next, we consider two types of edge defects that may give rise to the $1\times2$ zigzag reconstruction observed in STM: A periodic As vacancy on the upper terrace and a Mn vacancy in the lower MnAs layer (see Figs. 4(b, c)). The formation energies of As and Mn vacancies in the step edge model are presented in Table 1. Interestingly, we find that in this case the energetic favorability of the Mn and As vacancies at a step edge are reversed. Along the step edge, Mn vacancies are energetically unfavorable while As vacancies have negative formation energies. Therefore, we conclude that periodic As vacancies are the more likely explanation for the experimentally observed $1\times2$ reconstruction along the step edge.

![Figure 5](image.png)

**Figure 5:** (a) STM simulations at $-1$ V sample bias of a step edge with periodic As vacancies obtained from the atomic model shown in Fig. 4(b). (b) DOS calculated at 2 to 5 Å above the slab in vacuum for As near the zigzag edge (red cross) and As on the surface (blue cross).

Using the energetically favorable As vacancy step edge model, the STM image of the surface is simulated from our DFT charge density profiles. Figure 5a presents STM simulations for the step edge
with periodic As vacancies obtained with the P4VASP software [26], using an isosurface value of 141.2 Å³. The images show a zig-zag edge structure along the edge of As vacancies which resemble well the STM image shown in Figs. 3a,b. Furthermore, we plot the DOS calculated in vacuum, 2 to 5 Å above As at the zigzag step edge and As on the surface of the terrace (see Fig. 5b). DOS in vacuum was estimated using a similar method as described in Ref [27]. The energy resolved charge density in real space was calculated on a fine energy grid with 10 meV window, between -1 and 1 eV. For these calculations, we employed a 7 × 2 × 1 k-point grid and a 50 meV Gaussian broadening. The real space charge densities at specific heights above blue-As and red-As representing the DOS in vacuum, is comparable with the STS signal. We find that the vacuum DOS decreases exponentially with height – DOS at 3, 4, 5 Å are two, three and four orders of magnitude less than DOS at 2Å, respectively. For convenience, the DOS in vacuum for each height is normalized with the maximum DOS value corresponding to the specific height. Irrespective of the height, we find a significant increase in the DOS below the Fermi level for As at the step edge, which corresponds very well with our STS data in Fig. 3d.
**Figure 6:** Spin polarized PDOS for As and Mn near the step edge in upper MnAs. PDOS for Cu-$d$ and As-$p$ inside the slab are also shown for comparison.

Moreover, the contributions to the edge state at $-0.5$ eV are estimated through analyzing the spin polarized projected-DOS (PDOS), shown in Fig. 6. Specifically, we present the PDOS for As and Mn ions near the step edge in the upper MnAs layer (see Fig. 4b). We find that the edge state is predominantly comprised of As-$p$ and Mn-$d$ states, present near the step edge. The PDOS for Cu and As are also presented for comparison. Interestingly, while As-$p$ states in the bulk and inside the slab have small magnetic moment, $\sim 0.013$ $\mu$B, As-$p$ states at the surface are significantly spin polarized, with a net magnetic moment of $\sim 0.128$ $\mu$B. The highly asymmetric nature of the position of the As-ion – arising not only from the step edge but also from the adjacent As-vacancy – could be responsible for the 10-fold increase in the value of local magnetic moment for As ion at step edge compared with the bulk As. Given that CuMnAs can be a Dirac semimetal [8], these step edge states may have a topologically nontrivial nature [28]. However, further studies are needed to evaluate this behavior.

**Conclusion**

In summary, we report a detailed study on a tetragonal CuMnAs thin film grown on a GaP substrate using STM and ab initio calculations. The surface is found to be As-terminated with both 1×1 and 1×2 reconstruction domains. The clean surface has electronic density of states resembling those of a semimetal. The step edges exhibit a zigzag 1×2 reconstruction with edge states below the Fermi level. DFT calculations indicate that the zigzag reconstruction is due to the presence of As vacancies on the step edge and that these defects can give rise to the observed emergent edge states. This study provides the understanding of the surface and step edge structure of CuMnAs which enables future investigations on
its topological properties and magnetism as well as potential applications in topological antiferromagnetic spintronics [10].

Acknowledgement

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References


